U.S. PATENT DOCUMENTS

2010/0001300	A1	1/2010	Raring et al.
2010/0025656	A1	2/2010	Raring et al.
2010/0148145	A1	6/2010	Ishibashi et al.
2010/0219505	A1	9/2010	D'Evelyn et al.
2011/0056429	A1	3/2011	Raring et al.

OTHER PUBLICATIONS

Feezell et al., 'AlGaN-Cladding-Free Nonpolar InGaN/GaN Laser Diodes,' Japanese Journal of Applied Physics, vol. 46, No. 13, 2007, pp. L284-L286.

Haskell et al., 'Defect Reduction in (1100) m-plane gallium nitride via lateral epitaxial overgrowth by hydride vapor phase epitaxy', Applied Physics Letters 86, 111917 (2005), pp. 1-3.

Kojima et al., 'Stimulated Emission At 474 nm From an InGaN Laser Diode Structure Grown on A (1122) GaN Substrate,' Applied Physics Letters, vol. 91, 2007, pp. 251107-251107-3.

Kubota et al., 'Temperature Dependence of Polarized Photoluminescence From Nonpolar m-Plane InGaN Multiple Quantum Wells for Blue Laser Diodes,' Applied Physics Letter, vol. 92, 2008, pp. 011920-1-011920-3.

PCT Communication Including Partial Search and Examination Report for PCT/US2011/41106, dated Oct. 4, 2011, 2 pages total.

International Search Report for PCT application PCT/US2011/41106 (Jan. 5, 2012).

Tsuda et al., 'Blue Laser Diodes Fabricated on m-Plane GaN Substrates,' Applied Physics Express, vol. 1, 2008, pp. 011104-1-011104-3.

Tyagi et al., 'Semipolar (1011) InGaN/GaN Laser Diodes on Bulk GaN Substrates,' Japanese Journal of Applied Physics, vol. 46, No. 19, 2007, pp. L444-L445.

USPTO Office Action for U.S. Appl. No. 12/478,736 dated Feb. 7, 2012.

USPTO Office Action for U.S. Appl. No. 12/858,379 dated Apr. 14, 2011.

USPTO Notice of Allowance for U.S. Appl. No. 12/858,379 dated Dec. 6, 2011.

USPTO Notice of Allowance for U.S. Appl. No. 13/184,160 dated Dec. 12, 2011.